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(54) Title: SYSTEM AND METHOD TO FABRICATE MAGNETIC RANDOM ACCESS MEMORY

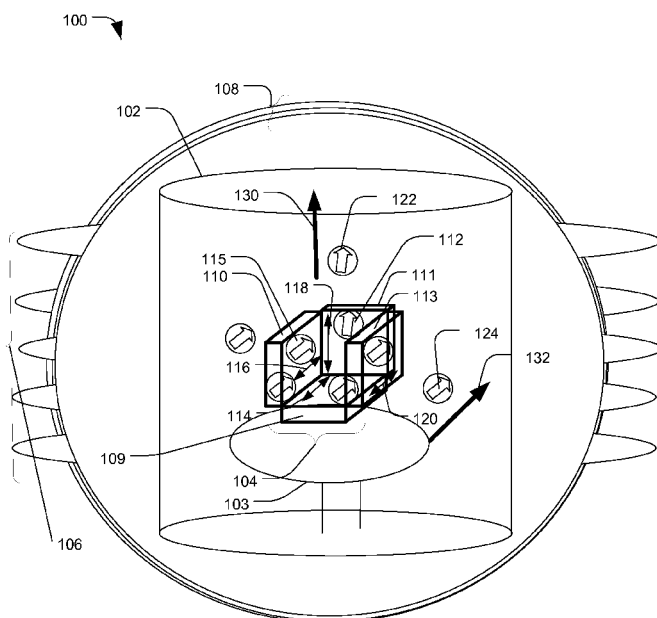


FIG. 1

(57) Abstract: A system and method to fabricate magnetic random access memory is disclosed. In particular, a method of aligning a magnetic film during deposition is disclosed. The method includes applying a first magnetic field along a first direction (130) in a region in which a substrate resides during a deposition of a first magnetic material onto the substrate. The method further includes applying a second magnetic field (132) along a second direction in the region during the deposition of the first magnetic material onto the substrate.



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